

Search History. (app.) *[Signature]* (4/29/05).

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	((("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306,211"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/04/29 07:11
L2	59	(US-20010015170-\$ or US-20020016085-\$ or US-20020094658-\$ or US-20020102862-\$ or US-20020124793-\$ or US-20020158311-\$ or US-20020158313-\$ or US-20020160605-\$ or US-20020182423-\$ or US-20020192918-\$ or US-20030054601-\$ or US-20040089918-\$ or US-20040161875-\$ or US-20040195655-\$ or US-20040198010-\$ or US-20040217430-\$ or US-20050006663-\$ or US-20050023642-\$ or US-20050051798-\$ or US-20050064645-\$ or US-20050082571-\$).did. or (US-5296258-\$ or US-5298452-\$ or US-5449923-\$ or US-5456762-\$ or US-5459089-\$ or US-5599403-\$ or US-5670414-\$ or US-5671914-\$ or US-5681402-\$ or US-5683934-\$ or US-5726440-\$ or US-5847418-\$ or US-5861324-\$ or US-5906680-\$ or US-6064081-\$ or US-6183857-\$ or US-6190975-\$ or US-6214107-\$ or US-6273950-\$ or US-6285064-\$ or US-6306211-\$ or US-6358773-\$ or US-6362065-\$ or US-6368888-\$ or US-6472594-\$ or US-6552375-\$).did. or (US-6673662-\$ or US-6750119-\$). did. or (JP-62216364-\$).did. or (DE-3777507-\$ or EP-703628-\$ or EP-829908-\$ or EP-908984-\$ or EP-1039512-\$ or US-20020016085-\$ or US-6285064-\$ or US-6358773-\$ or US-20020102862-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/04/29 07:14
L3	0	("2andkanazawa.in:").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:14

L4	0	2 and kanazawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:15
L5	2	2 and nakazawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:15
L6	2120	((257/77) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/04/29 08:04
L7	355	6 and silicon adj carbide and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:31
L8	10	6 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 08:05
L9	2300	((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/04/29 08:04
L10	180	9 NOT 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 08:05
L11	0	10 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 08:05
S1	4	"775514".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:11
S2	6	((("6,285,064") or ("6,358,773") or ("6,368,888"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:06
S3	1	(US-20040161875-\$).did.	US-PGPUB	OR	OFF	2005/04/03 22:08

S4	10	(silicon adj carbide sic) near20 graded near20 buffer and single adj (crystalline crystal) near4 (silicon si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:13
S5	2	(silicon adj carbide sic) near20 graded near20 buffer and single adj (crystalline crystal) near4 (silicon si) and (thick thickness) near10 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:18
S6	2	("6750119").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:18
S7	1	"5683934".PN.	USPAT; USOCR	OR	OFF	2005/04/03 22:19
S8	1	"5906680".PN.	USPAT; USOCR	OR	OFF	2005/04/03 22:19
S9	1	"6190975".PN.	USPAT; USOCR	OR	OFF	2005/04/03 22:20
S10	1	"20020160605".PN.	US-PGPUB	OR	OFF	2005/04/03 22:20
S11	155	junction near4 (sic silicon adj carbide) near4 (si silicon) and (monocrystalline single adj (crystal crystalline))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 09:50
S12	15	(US-20010015170-\$).did. or (US-6472594-\$ or US-6273950-\$ or US-6214107-\$ or US-6183857-\$ or US-5861324-\$ or US-5847418-\$ or US-5726440-\$ or US-5681402-\$ or US-5671914-\$ or US-5599403-\$ or US-5459089-\$ or US-5456762-\$ or US-5449923-\$).did. or (JP-62216364-\$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2005/04/04 09:49
S13	144	S11 and (interface thick thickness abrupt sharp buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 09:51
S14	14	S12 and (interface thick thickness abrupt sharp buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 09:51
S15	7	S12 and (interface thick thickness abrupt sharp buffer) and ("SiC/Si" "Si/SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:13

S16	3	((("5298452") or ("5906680"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 10:01
S17	0	(257/77anduhf-cvdand("S/SiC""SiC/S")).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 10:02
S18	0	257/77 and uhf-cvd and ("S/SiC""SiC/S")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 10:02
S19	0	257/77 and uhf-cvd and ("S/SiC""SiC/S")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:02
S20	0	257/77 and uhf near1 cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S21	0	257/77 and uhf adj.cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S22	0	257/77.ccls. and uhf adj cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S23	3	257/77.ccls. and uhf and cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S24	1260	((257/77) or (438/931)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:26
S25	47	S24 and ("Si/SiC" "SiC/S" interface junction) near10 (abrupt sharp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:24

S26	5	S24 and hbt and buffer and graded and (thick thickness thin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:40
S27	0	(single adj (crystalline crystal) monocrystalline) near3 (silicon "Si") near6 (silicon adj carbide "SiC") and graded near4 ("Si.sub."\$3"C.sub."\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:44
S28	363	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:45
S29	0	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and (buffer graded) near4 ("Si.sub.xC.sub.1-x" "Si.sub.1-xC.sub.x")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:46
S30	0	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and "Si.sub."\$3"C.sub."\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:47
S31	363	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:48
S32	179	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") not (silicon adj carbide adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 12:19
S33	10	((("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306,211"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:24
S34	10	((("5,906,680") or ("6,190,975") or ("5,683,934") or ("20020016085") or ("6,306,211"))).PN. or (2001/0160605).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:24
S35	0	("20010160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:25

S36	0	(2001/0160605).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:25
S37	85	kanazawa.in. and 200210\$2.pd.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:26
S38	273	kanazawa.in. and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:26
S39	31	kanazawa.in. and silicon	US-PGPUB	OR	OFF	2005/04/04 12:31
S40	26	kanazawa.in. and silicon and substrate	US-PGPUB	OR	OFF	2005/04/04 12:26
S41	0	@pd=200210\$2 and kanazawa.in.	US-PGPUB	OR	OFF	2005/04/04 12:31
S42	202	kanazawa.in.	US-PGPUB	OR	OFF	2005/04/04 12:32
S43	4	suemitsu.in. and sic adj. film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:53
S44	0	suemitsu.in. and nakazaka.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:53
S45	4	suemitsu.in. and nakazawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:59
S46	0	("20010160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:58
S47	2	("2001160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:58
S48	15481	nakazawa.in.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:59



S49	125	nakazawa.in. and 200210\$2.pd.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:01
S50	187	nakazawa.in. and substrate	US-PGPUB	OR	OFF	2005/04/04 13:57
S51	0	(2004/0161875).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:57
S52	2	("20040161875").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:58
S53	2	("20070161875").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:58
S54	0	("20010160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:59
S55	0	("(monocrystallinesingleadjcrystal) near2(siliconSi)and(carbonC)and(c oncentrationprofile)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 10:25
S56	8580	(monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26
S57	1322	(monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron near5 (barrier diffusion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26
S58	85	(monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron near5 (barrier diffusion) and (hbt heterojunction adj bipolar adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:27
S59	456	gated adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 12:14

S60	73	gated adj diode.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 12:15
S61	3	"751714".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 12:16
S62	46	boron near1 diffusion and (silicon adj carbide SiC) and concentration near3 profile and (silicon Si) near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:55
S63	0	intrinsic adj buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:57
S64	188	buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:23
S65	0	collector near4 lattice and S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:23
S66	0	collector near10 lattice and S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:23
S67	8	collector near10 lattice and S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:23
S68	27	(single adj crystalline monocrystalline) near2 emitter and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:32
S69	1	(single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity) and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05



S70	13	(single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05
S71	88	polycrystalline near3 emitter and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 12:44
S72	27	polycrystalline near3 emitter and hbt and (carbide SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:45
S73	1	polycrystalline near3 (carbide SiC) near4 emitter and hbt and (carbide SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:46
S74	1	polycrystalline near3 (carbide SiC) near4 emitter and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:46
S75	2	("6137120").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 13:09
S76	95	fang.in. and emitter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 13:10